8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Rev. 5 — 27 December 2012

Product data sheet

1. General description

The 74AVC8T245 is an 8-bit, dual supply transceiver that enables bidirectional level translation. It features two 8-bit input-output ports (An and Bn), a direction control input (DIR), a output enable input (\overline{OE}) and dual supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins An, \overline{OE} and DIR are referenced to $V_{CC(A)}$ and pins Bn are referenced to $V_{CC(B)}$. A HIGH on DIR allows transmission from An to Bn and a LOW on DIR allows transmission from Bn to An. The output enable input (\overline{OE}) can be used to disable the outputs so the buses are effectively isolated.

The device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either V_{CC(A)} or V_{CC(B)} are at GND level, both An and Bn are in the high-impedance OFF-state.

2. Features and benefits

- Wide supply voltage range:
 - V_{CC(A)}: 0.8 V to 3.6 V
 - V_{CC(B)}: 0.8 V to 3.6 V
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114E Class 3B exceeds 8000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Maximum data rates:
 - ◆ 380 Mbit/s (≥ 1.8 V to 3.3 V translation)
 - ◆ 260 Mbit/s (≥ 1.1 V to 3.3 V translation)
 - ◆ 260 Mbit/s (≥ 1.1 V to 2.5 V translation)
 - ◆ 210 Mbit/s (≥ 1.1 V to 1.8 V translation)
 - 150 Mbit/s (\geq 1.1 V to 1.5 V translation)
 - ◆ 100 Mbit/s (≥ 1.1 V to 1.2 V translation)



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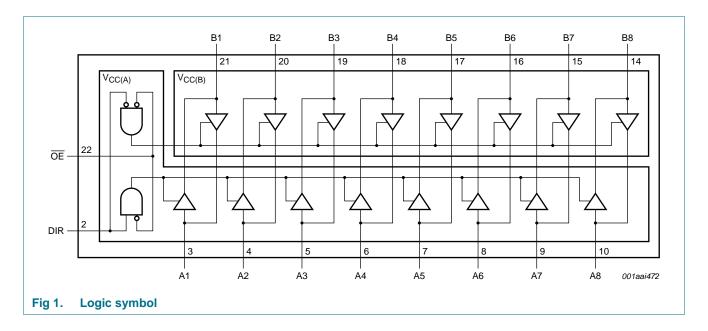
- Suspend mode
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1.Ordering information

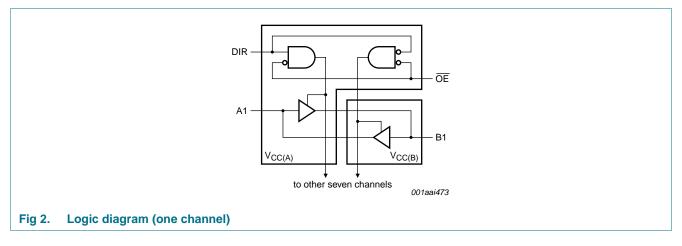
Type number	Package			
	Temperature range	Name	Description	Version
74AVC8T245PW	–40 °C to +125 °C	TSSOP24	plastic thin shrink small outline package; 24 leads; body width 4.4 mm	SOT355-1
74AVC8T245BQ	–40 °C to +125 °C	DHVQFN24	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body $3.5 \times 5.5 \times 0.85$ mm	SOT815-1

4. Functional diagram

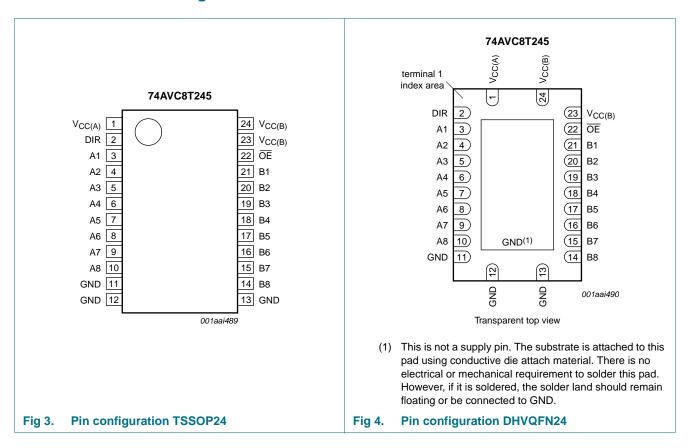


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5. Pinning information



5.1 Pinning

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Table 2.	Pin description	
Symbol	Pin	Description
V _{CC(A)}	1	supply voltage A (An, $\overline{\text{OE}}$ and DIR inputs are referenced to $V_{\text{CC(A)}}$
DIR	2	direction control
A1 to A8	3, 4, 5, 6, 7, 8, 9, 10	data input or output
GND ^[1]	11	ground (0 V)
GND ^[1]	12	ground (0 V)
GND ^[1]	13	ground (0 V)
B1 to B8	21, 20, 19, 18, 17, 16, 15, 14	data input or output
OE	22	output enable input (active LOW)
V _{CC(B)}	23	supply voltage B (Bn inputs are referenced to $V_{CC(B)}$)
V _{CC(B)}	24	supply voltage B (Bn inputs are referenced to $V_{CC(B)}$)

5.2 Pin description

[1] All GND pins must be connected to ground (0 V).

6. Functional description

Table 3. Function table^[1]

Supply voltage	Input		Input/output ^[3]	
V _{CC(A)} , V _{CC(B)}	OE ^[2]	DIR ^[2]	An ^[2]	Bn
0.8 V to 3.6 V	L	L	An = Bn	input
0.8 V to 3.6 V	L	Н	input	Bn = An
0.8 V to 3.6 V	Н	Х	Z	Z
GND[<u>3]</u>	Х	Х	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] The An, DIR and $\overline{\text{OE}}$ input circuit is referenced to V_{CC(A)}; The Bn input circuit is referenced to V_{CC(B)}.

[3] If at least one of $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into suspend mode.

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CC(A)}	supply voltage A		-0.5	+4.6	V
V _{CC(B)}	supply voltage B		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
Ι _{ΟΚ}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode	<u>[1][2][3]</u> –0.5	$V_{CCO} + 0.5$	V
		Suspend or 3-state mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current	per $V_{CC(A)}$ or $V_{CC(B)}$ pin	-	100	mA

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Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
I _{GND}	ground current	per GND pin	-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	<u>[4]</u> _	500	mW

[1] The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V_{CCO} is the supply voltage associated with the output port.

[3] V_{CCO} + 0.5 V should not exceed 4.6 V.

[4] For TSSOP24 package: P_{tot} derates linearly at 5.5 mW/K above 60 °C.
 For DHVQFN24 package: P_{tot} derates linearly at 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5.	Recommended operating condition	ons			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		0.8	3.6	V
V _{CC(B)}	supply voltage B		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	<u>[1]</u> 0	V _{cco}	V
		Suspend or 3-state mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CCI} = 0.8 \text{ V} \text{ to } 3.6 \text{ V}$	[2] _	5	ns/V

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the input port.

9. Static characteristics

Table 6. Typical static characteristics at $T_{amb} = 25 \text{ °C} \frac{[1][2]}{2}$

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O} = -1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.69	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 1.5 mA; $V_{CC(A)} = V_{CC(B)} = 0.8$ V	-	0.07	-	V
l _l	input leakage current	DIR, \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V	-	±0.025	±0.25	μΑ
I _{OZ}	OFF-state output current	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	<u>[3]</u> _	±0.5	±2.5	μΑ
		suspend mode A port; V _O = 0 V or V _{CCO} ; V _{CC(A)} = 3.6 V; V _{CC(B)} = 0 V	<u>[3]</u> _	±0.5	±2.5	μΑ
		suspend mode B port; V _O = 0 V or V _{CCO} ; V _{CC(A)} = 0 V; V _{CC(B)} = 3.6 V	<u>[3]</u> _	±0.5	±2.5	μΑ

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At recom	mended operating conditions	s; voltages are referenced to GND (ground = 0 V).				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{OFF}	power-off leakage current	A port; V _I or V _O = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0.8 V to 3.6 V	-	±0.1	±1	μΑ
		B port; V _I or V _O = 0 V to 3.6 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0.8 V to 3.6 V	-	±0.1	±1	μΑ
CI	input capacitance	DIR, \overline{OE} input; V _I = 0 V or 3.3 V; V _{CC(A)} = V _{CC(B)} = 3.3 V	-	1.5	-	pF
C _{I/O}	input/output capacitance	A and B port; $V_O = 3.3$ V or 0 V; $V_{CC(A)} = V_{CC(B)} = 3.3$ V	-	4.3	-	pF

Table 6. Typical static characteristics at $T_{amb} = 25 \text{ °C}[1][2]$...continued At recommended operating conditions: voltages are referenced to GND (around = 0)

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the data input port.

[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Table 7. Static characteristics [1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C t	o +85 °C	–40 °C to	o +125 °C	Unit
			Min	Max	Min	Max	
V _{IH}	HIGH-level	data input					
	input voltage	$V_{CCI} = 0.8 V$	0.70V _{CCI}	-	0.70V _{CCI}	-	V
		V _{CCI} = 1.1 V to 1.95 V	$0.65V_{CCI}$	-	$0.65V_{CCI}$	-	V
		V_{CCI} = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		$V_{CCI} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2	-	2	-	V
		DIR, \overline{OE} input					
		$V_{CC(A)} = 0.8 V$	0.70V _{CC(A)}	-	0.70V _{CC(A)}	-	V
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	0.65V _{CC(A)}	-	0.65V _{CC(A)}	-	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	1.6	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V
V _{IL}	LOW-level	data input					
	input voltage	$V_{CCI} = 0.8 V$	-	$0.30V_{CCI}$	-	0.30V _{CCI}	V
		V _{CCI} = 1.1 V to 1.95 V	-	$0.35V_{CCI}$	-	$0.35V_{CCI}$	V
		V_{CCI} = 2.3 V to 2.7 V	-	0.7	-	0.7	V
		V_{CCI} = 3.0 V to 3.6 V	-	0.8	-	0.8	V
		DIR, \overline{OE} input					
		$V_{CC(A)} = 0.8 V$	-	0.30V _{CC(A)}	-	0.30V _{CC(A)}	V
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	-	0.35V _{CC(A)}	-	0.35V _{CC(A)}	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	-	0.8	-	0.8	V

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Symbol	Parameter	Conditions	–40 °C to	• +85 °C	–40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$			1		l
	output voltage	$I_{O} = -100 \ \mu\text{A};$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ \text{V to } 3.6 \ \text{V}$	V _{CCO} – 0.1	-	$V_{CCO}-0.1$	-	V
		$I_{O} = -3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	0.85	-	V
		$ I_O = -6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V} $	1.05	-	1.05	-	V
		$I_{O} = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	1.2	-	V
		$I_{O} = -9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	1.75	-	V
		$I_{O} = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	V
V _{OL} LOW-level		$V_{I} = V_{IH} \text{ or } V_{IL}$					
ou	output voltage	$I_{O} = 100 \ \mu\text{A};$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ \text{V to } 3.6 \ \text{V}$	-	0.1	-	0.1	V
		$I_O = 3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	-	0.25	-	0.25	V
		$I_{O} = 6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	0.35	-	0.35	V
		$I_{O} = 8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	-	0.45	-	0.45	V
		$I_{O} = 9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	-	0.55	-	0.55	V
		$I_{O} = 12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	-	0.7	-	0.7	V
I _I	input leakage current	DIR, \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V	-	±1	-	±5	μA
I _{OZ}	OFF-state output current	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	<u>[3]</u>	±5	-	±30	μA
		suspend mode A port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 3.6 \text{ V};$ $V_{CC(B)} = 0 \text{ V}$	<u>[3]</u>	±5	-	±30	μA
		suspend mode B port; $V_O = 0 V \text{ or } V_{CCO}; V_{CC(A)} = 0 V;$ $V_{CC(B)} = 3.6 V$	[3] -	±5	-	±30	μA
I _{OFF}	power-off leakage	A port; V ₁ or V ₀ = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0.8 V to 3.6 V	-	±5	-	±30	μΑ
	current	B port; V ₁ or V ₀ = 0 V to 3.6 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0.8 V to 3.6 V	-	±5	-	±30	μA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

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Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
			Min	Max	Min	Max	
I _{CC}	supply current	A port; $V_I = 0$ V or V_{CCI} ; $I_O = 0$ A			1		
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	10	-	55	μA
		$V_{CC(A)} = 1.1 V \text{ to } 3.6 V;$ $V_{CC(B)} = 1.1 V \text{ to } 3.6 V$	-	8	-	50	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	8	-	50	μA
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$	-2	-	-12	-	μA
		B port; $V_I = 0$ V or V_{CCI} ; $I_O = 0$ A					
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	10	-	55	μA
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	8	-	50	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-2	-	-12	-	μA
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$	-	8	-	50	μA
		A plus B port $(I_{CC(A)} + I_{CC(B)});$ $I_O = 0 A; V_I = 0 V \text{ or } V_{CCI};$ $V_{CC(A)} = 0.8 V \text{ to } 3.6 V;$ $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	20	-	70	μA
		A plus B port $(I_{CC(A)} + I_{CC(B)});$ $I_O = 0 A; V_I = 0 V \text{ or } V_{CCI};$ $V_{CC(A)} = 1.1 V \text{ to } 3.6 V;$ $V_{CC(B)} = 1.1 V \text{ to } 3.6 V$	-	16	-	65	μA

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the data input port.

[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Table 8. Typical total supply current (I_{CC(A)} + I_{CC(B)})

V _{CC(A)}	V _{CC(B)}						Unit	
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μΑ
0.8 V	0.1	0.1	0.1	0.1	0.1	0.3	1.6	μΑ
1.2 V	0.1	0.1	0.1	0.1	0.1	0.1	0.8	μΑ
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.4	μΑ
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.2	μΑ
2.5 V	0.1	0.3	0.1	0.1	0.1	0.1	0.1	μΑ
3.3 V	0.1	1.6	0.8	0.4	0.2	0.1	0.1	μΑ

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10. Dynamic characteristics

Table 9. Typical dynamic characteristics at $V_{CC(A)} = 0.8$ V and $T_{amb} = 25$ °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

Symbol	Parameter	Conditions			Vco	С(В)			Unit
		0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V		
t _{pd}	t _{pd} propagation delay	An to Bn	14.4	7.0	6.2	6.0	5.9	6.0	ns
		Bn to An	14.4	12.4	12.1	11.9	11.8	11.8	ns
t _{dis}	disable time	OE to An	16.2	16.2	16.2	16.2	16.2	16.2	ns
		OE to Bn	17.6	10.0	9.0	9.1	8.7	9.3	ns
t _{en}	enable time	OE to An	21.9	21.9	21.9	21.9	21.9	21.9	ns
		OE to Bn	22.2	11.1	9.8	9.4	9.4	9.6	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Table 10. Typical dynamic characteristics at $V_{CC(B)} = 0.8$ V and $T_{amb} = 25$ °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

Symbol	Parameter	Conditions			Vc	C(A)			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd} propagation delay	An to Bn	14.4	12.4	12.1	11.9	11.8	11.8	ns	
	Bn to An	14.4	7.0	6.2	6.0	5.9	6.0	ns	
t _{dis}	disable time	OE to An	16.2	5.9	4.4	4.2	3.1	3.5	ns
		OE to Bn	17.6	14.2	13.7	13.6	13.3	13.1	ns
t _{en}	enable time	OE to An	21.9	6.4	4.4	3.5	2.6	2.3	ns
	OE to Bn	22.2	17.7	17.2	17.0	16.8	16.7	ns	

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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Symbol	Parameter	Conditions			V _{CC(A)} =	= V _{CC(B)}			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C _{PD} power dissipation capacitance		A port: (direction An to Bn); output enabled	0.2	0.2	0.2	0.3	0.4	0.5	pF
	A port: (direction An to Bn); output disabled	0.2	0.2	0.2	0.3	0.4	0.5	pF	
	A port: (direction Bn to An); output enabled	9	9	10	10	11	13	pF	
		A port: (direction Bn to An); output disabled	0.6	0.6	0.6	0.7	0.7	0.8	pF
		B port: (direction An to Bn); output enabled	9	9	10	10	11	13	pF
		B port: (direction An to Bn); output disabled	0.6	0.6	0.6	0.7	0.7	0.8	pF
		B port: (direction Bn to An); output enabled	0.2	0.2	0.2	0.3	0.4	0.5	pF
		B port: (direction Bn to An); output disabled	0.2	0.2	0.2	0.3	0.4	0.5	pF

Table 11. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \text{ °C } [1][2]$ Voltages are referenced to GND (ground = 0 V).

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $\mathsf{P}_{\mathsf{D}} = \mathsf{C}_{\mathsf{P}\mathsf{D}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}^2 \times \mathsf{f}_i \times \mathsf{N} + \Sigma(\mathsf{C}_{\mathsf{L}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}^2 \times \mathsf{f}_o) \text{ where:}$

 $f_i = input frequency in MHz;$

 f_o = output frequency in MHz;

 C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

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Symbol	Parameter	Conditions					Vc	C(B)					Uni
			1.2 V :	± 0.1 V	1.5 V :	± 0.1 V	1	0.15 V	2.5 V :	± 0.2 V	3.3 V :	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V												
t _{pd}	propagation	An to Bn	0.5	9.0	0.5	6.7	0.5	5.8	0.5	4.9	0.5	4.8	ns
	delay	Bn to An	0.5	9.0	0.5	8.5	0.5	8.3	0.5	8.0	0.5	7.8	ns
t _{dis}	disable time	OE to An	0.5	11.8	0.5	11.8	0.5	11.8	0.5	11.8	0.5	11.8	ns
		OE to Bn	0.5	12.3	0.5	9.5	0.5	9.4	0.5	8.0	0.5	8.9	ns
t _{en} enable tii	enable time	OE to An	1.1	14.4	1.1	14.4	1.1	14.4	1.1	14.4	1.1	14.4	ns
		OE to Bn	1.1	14.2	1.1	10.4	1.1	9.0	1.0	7.7	1.0	7.3	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd} propagation delay	propagation	An to Bn	0.5	8.5	0.5	5.6	0.5	4.7	0.5	4.4	0.5	4.1	ns
	delay	Bn to An	0.5	6.7	0.5	5.6	0.5	5.3	0.5	5.2	0.5	5.0	ns
t _{dis} di	disable time	OE to An	0.5	8.6	0.5	8.6	0.5	8.6	0.5	8.6	0.5	8.6	ns
		OE to Bn	0.5	11.2	0.5	8.4	0.5	7.6	0.5	7.2	0.5	7.8	ns
t _{en}	enable time	OE to An	1.1	8.7	1.1	8.7	1.1	8.7	1.1	8.7	1.1	8.7	ns
		OE to Bn	1.1	12.8	1.1	8.1	1.1	7.1	1.0	5.6	1.0	5.2	ns
V _{CC(A)} =	1.65 V to 1.95	V											
t _{pd}	propagation	An to Bn	0.5	8.3	0.5	5.3	0.5	4.5	0.5	3.8	0.5	3.5	ns
	delay	Bn to An	0.5	5.8	0.5	4.7	0.5	4.5	0.5	4.3	0.5	4.1	ns
t _{dis}	disable time	OE to An	0.5	7.1	0.5	7.1	0.5	7.1	0.5	7.1	0.5	7.1	ns
		OE to Bn	0.5	10.9	0.5	7.8	0.5	6.9	0.5	6.0	0.5	5.8	ns
t _{en}	enable time	OE to An	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	ns
		OE to Bn	1.1	12.4	1.1	8.2	1.0	6.7	0.5	5.1	0.5	4.5	ns
$V_{CC(A)} =$	2.3 V to 2.7 V												
t _{pd}	propagation	An to Bn	0.5	8.0	0.5	5.2	0.5	4.3	0.5	3.3	0.5	2.9	ns
	delay	Bn to An	0.5	4.9	0.5	4.4	0.5	3.8	0.5	3.3	0.5	3.1	ns
t _{dis}	disable time	OE to An	0.5	5.1	0.5	5.1	0.5	5.1	0.5	5.1	0.5	5.1	ns
		OE to Bn	0.5	10.4	0.5	7.1	0.5	6.3	0.5	5.1	0.5	5.2	ns
t _{en}	enable time	OE to An	0.5	4.8	0.5	4.8	0.5	4.8	0.5	4.8	0.5	4.8	ns
		OE to Bn	1.1	11.9	1.1	7.9	0.5	6.4	0.5	4.6	0.5	4.0	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t _{pd}	propagation	An to Bn	0.5	7.8	0.5	5.0	0.5	4.1	0.5	3.1	0.5	2.7	ns
	delay	Bn to An	0.5	4.8	0.5	4.1	0.5	3.5	0.5	2.9	0.5	2.7	ns
t _{dis}	disable time	OE to An	0.5	4.9	0.5	4.9	0.5	4.9	0.5	4.9	0.5	4.9	ns
		OE to Bn	0.5	10.1	0.5	6.9	0.5	6.0	0.5	4.8	0.5	5.0	ns
t _{en}	enable time	OE to An	0.5	4.0	0.5	4.0	0.5	4.0	0.5	4.0	0.5	4.0	ns
•en		OE to Bn	1.1	11.7	1.1	7.8	0.5	6.2	0.5	4.5	0.5	3.9	ns

Table 12. Dynamic characteristics for temperature range -40 °C to +85 °C [1]

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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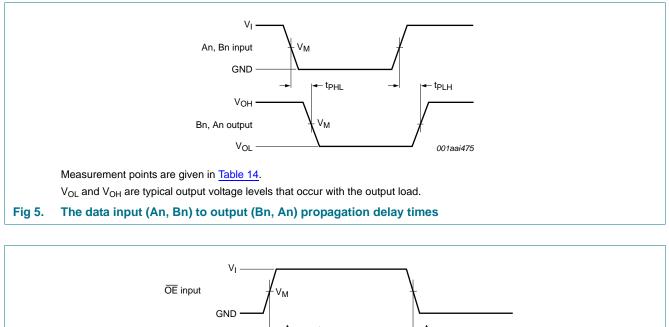
Symbol	Parameter	Conditions					Vc	C(B)					Uni
			1.2 V :	± 0.1 V	1.5 V :	± 0.1 V		0.15 V	2.5 V	± 0.2 V	3.3 V :	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V									•		•	
t _{pd}	propagation	An to Bn	0.5	9.9	0.5	7.4	0.5	6.4	0.5	5.4	0.5	5.3	ns
	delay	Bn to An	0.5	9.9	0.5	9.4	0.5	9.2	0.5	8.8	0.5	8.6	ns
t _{dis}	disable time	OE to An	0.5	13.0	0.5	13.0	0.5	13.0	0.5	13.0	0.5	13.0	ns
		OE to Bn	0.5	13.6	0.5	10.5	0.5	10.4	0.5	8.8	0.5	9.8	ns
enable time	enable time	OE to An	1.1	15.9	1.1	15.9	1.1	15.9	1.1	15.9	1.1	15.9	ns
	OE to Bn	1.1	15.7	1.1	11.5	1.1	9.9	1.0	8.5	1.0	8.1	ns	
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd} propaga delay	propagation	An to Bn	0.5	9.4	0.5	6.2	0.5	5.2	0.5	4.9	0.5	4.6	ns
	delay	Bn to An	0.5	7.4	0.5	6.2	0.5	5.9	0.5	5.8	0.5	5.5	ns
t _{dis} disa	disable time	OE to An	0.5	9.5	0.5	9.5	0.5	9.5	0.5	9.5	0.5	9.5	ns
		OE to Bn	0.5	12.4	0.5	9.3	0.5	8.4	0.5	8.0	0.5	8.6	ns
t _{en} e	enable time	OE to An	1.1	9.6	1.1	9.6	1.1	9.6	1.1	9.6	1.1	9.6	ns
		OE to Bn	1.1	14.1	1.1	9.0	1.1	7.9	1.0	6.2	1.0	5.8	ns
$V_{CC(A)} =$	1.65 V to 1.95	V											
t _{pd}	propagation	An to Bn	0.5	9.2	0.5	5.9	0.5	5.0	0.5	4.2	0.5	3.9	ns
	delay	Bn to An	0.5	6.4	0.5	5.2	0.5	5.0	0.5	4.8	0.5	4.6	ns
t _{dis}	disable time	OE to An	0.5	7.9	0.5	7.9	0.5	7.9	0.5	7.9	0.5	7.9	ns
		OE to Bn	0.5	12.0	0.5	8.6	0.5	7.6	0.5	6.6	0.5	6.4	ns
t _{en}	enable time	OE to An	1.0	7.5	1.0	7.5	1.0	7.5	1.0	7.5	1.0	7.5	ns
		OE to Bn	1.1	13.7	1.1	9.1	1.0	7.4	0.5	5.7	0.5	5.0	ns
$V_{CC(A)} =$	2.3 V to 2.7 V												
t _{pd}	propagation	An to Bn	0.5	8.8	0.5	5.8	0.5	4.8	0.5	3.7	0.5	3.2	ns
	delay	Bn to An	0.5	5.4	0.5	4.9	0.5	4.2	0.5	3.7	0.5	3.5	ns
t _{dis}	disable time	OE to An	0.5	5.7	0.5	5.7	0.5	5.7	0.5	5.7	0.5	5.7	ns
		OE to Bn	0.5	11.5	0.5	7.9	0.5	7.0	0.5	5.7	0.5	5.8	ns
t _{en}	enable time	OE to An	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	ns
		OE to Bn	1.1	13.1	1.1	8.7	0.5	7.1	0.5	5.1	0.5	4.4	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t _{pd}	propagation	An to Bn	0.5	8.6	0.5	5.5	0.5	4.6	0.5	3.5	0.5	3.0	ns
	delay	Bn to An	0.5	5.3	0.5	4.6	0.5	3.9	0.5	3.2	0.5	3.0	ns
t _{dis}	disable time	OE to An	0.5	5.4	0.5	5.4	0.5	5.4	0.5	5.4	0.5	5.4	ns
		OE to Bn	0.5	11.2	0.5	7.6	0.5	6.6	0.5	5.3	0.5	5.5	ns
t _{en}	enable time	OE to An	0.5	4.4	0.5	4.4	0.5	4.4	0.5	4.4	0.5	4.4	ns
•en			-		-		-		-		-		-

Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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11. Waveforms



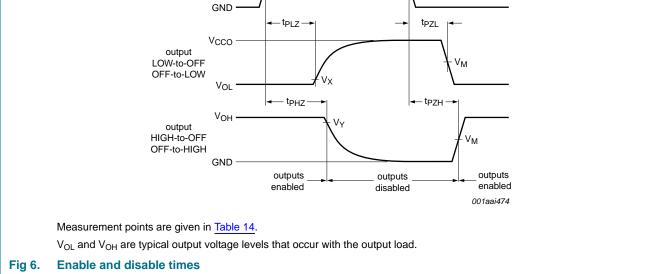


Table 14. Measurement points

Supply voltage	Input ^[1]	Output ^[2]		
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y
0.8 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} – 0.1 V
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] V_{CCO} is the supply voltage associated with the output port.

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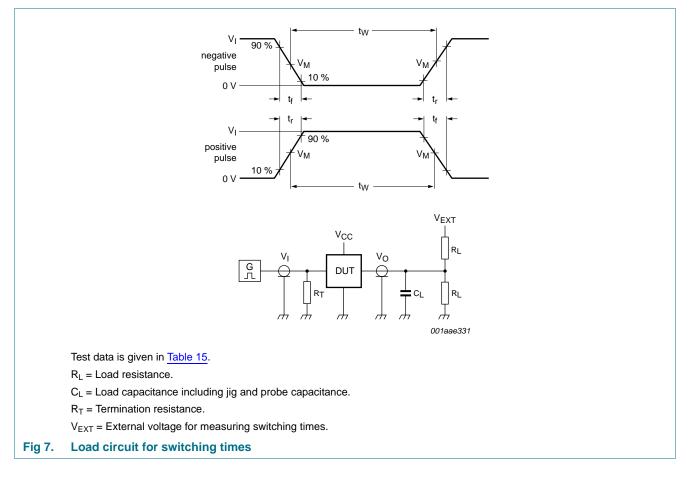


Table 15. Test data

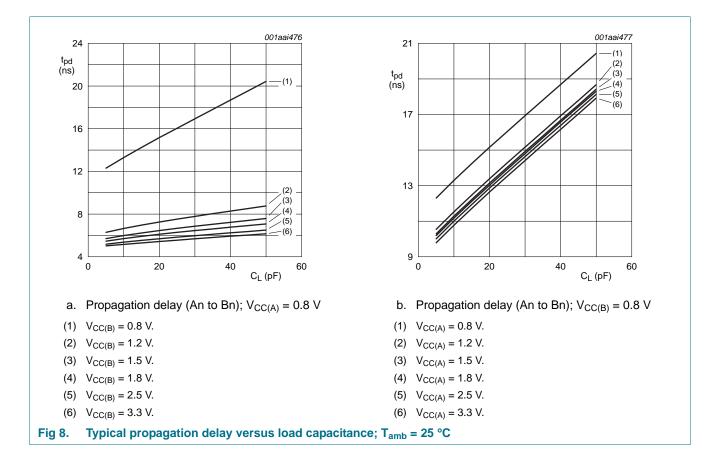
Supply voltage	Input		Load	Load		V _{EXT}			
$V_{CC(A)}, V_{CC(B)}$	V <mark>[^{1]}</mark>	∆t/∆V[2]	CL	RL	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]		
0.8 V to 1.6 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}		
1.65 V to 2.7 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}		
3.0 V to 3.6 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}		

[1] V_{CCI} is the supply voltage associated with the data input port.

 $[2] \quad dV/dt \geq 1.0 \ V/ns$

[3] V_{CCO} is the supply voltage associated with the output port.

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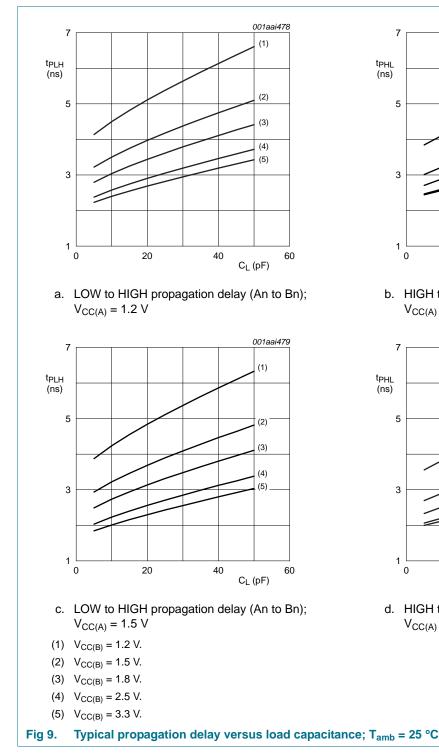


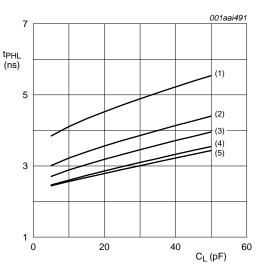
12. Typical propagation delay characteristics

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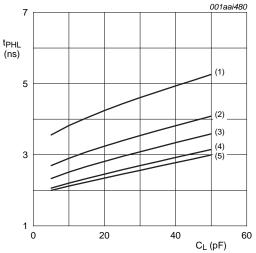
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b. HIGH to LOW propagation delay (An to Bn); $V_{CC(A)} = 1.2 \text{ V}$

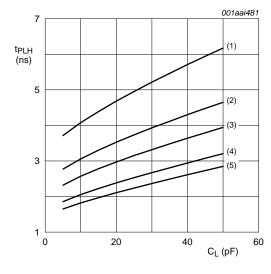


d. HIGH to LOW propagation delay (An to Bn); $V_{CC(A)} = 1.5 \text{ V}$

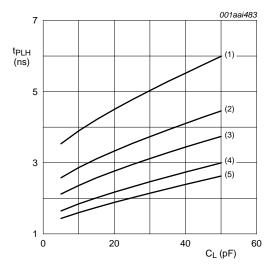
74AVC8T245 Product data sheet

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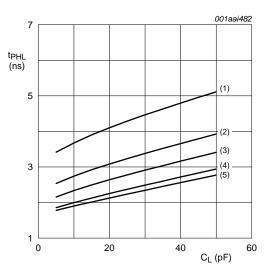


a. LOW to HIGH propagation delay (An to Bn); $V_{CC(A)}$ = 1.8 V

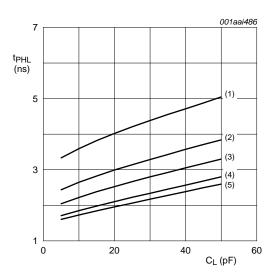


- c. LOW to HIGH propagation delay (An to Bn); $V_{CC(A)}$ = 2.5 V
- (1) $V_{CC(B)} = 1.2$ V.
- (2) V_{CC(B)} = 1.5 V.
- (3) $V_{CC(B)} = 1.8$ V.
- (4) $V_{CC(B)} = 2.5$ V.
- (5) $V_{CC(B)} = 3.3$ V.

Fig 10. Typical propagation delay versus load capacitance; T_{amb} = 25 °C



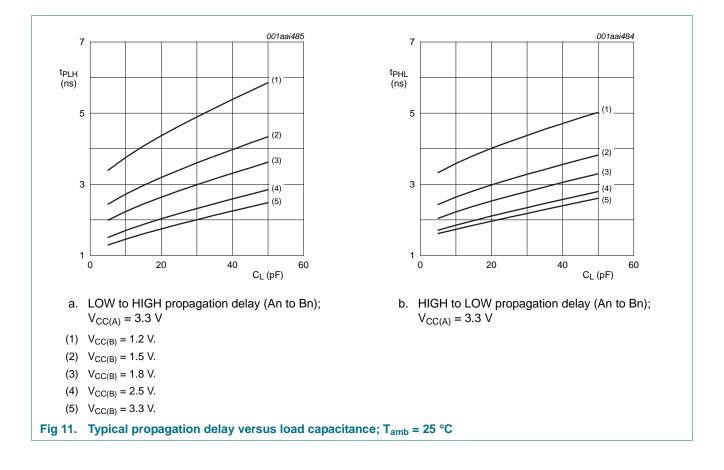
b. HIGH to LOW propagation delay (An to Bn); $V_{CC(A)}$ = 1.8 V



d. HIGH to LOW propagation delay (An to Bn); $V_{CC(A)} = 2.5 \text{ V}$

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13. Package outline

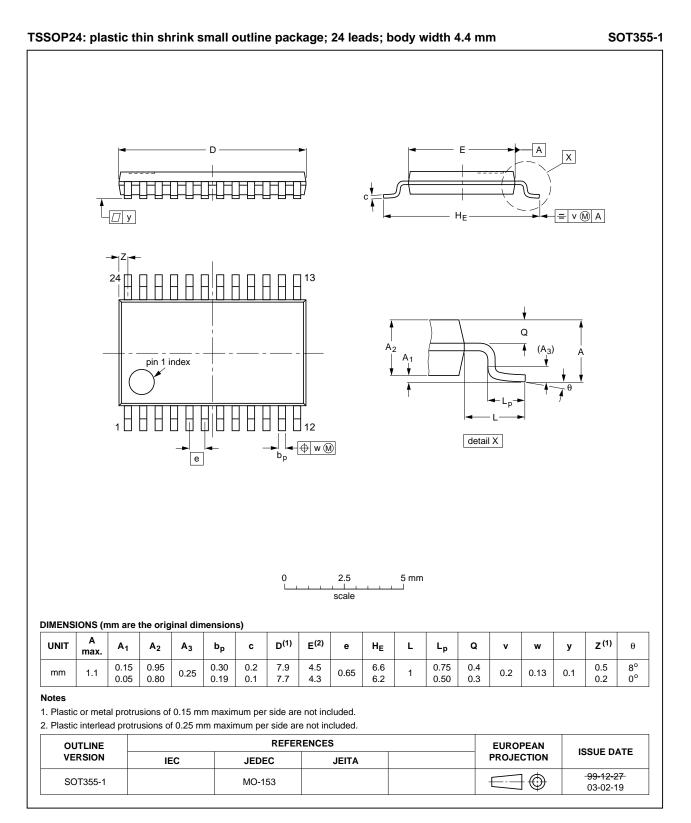
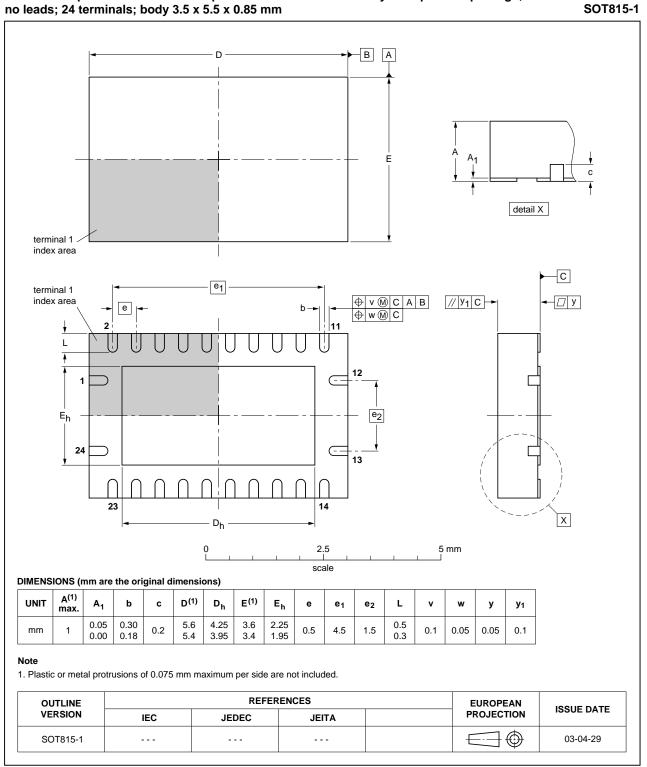


Fig 12. Package outline SOT355-1 (TSSOP24)

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DHVQFN24: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body 3.5 x 5.5 x 0.85 mm

Fig 13. Package outline SOT815-1 (DHVQFN24)

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14. Abbreviations

Table 16.	Abbreviations
Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
-	

15. Revision history

Table 17. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVC8T245 v.5	20121227	Product data sheet	-	74AVC8T245 v.4
Modifications:	• <u>Table 4</u> : cor	nditions I_{CC} and I_{GND} chang	ed (errata).	
74AVC8T245 v.4	20111208	Product data sheet	-	74AVC8T245 v.3
Modifications:	 Legal pages 	s updated.		
74AVC8T245 v.3	20110928	Product data sheet	-	74AVC8T245 v.2
74AVC8T245 v.2	20090428	Product data sheet	-	74AVC8T245 v.1
74AVC8T245 v.1	20080711	Product data sheet	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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